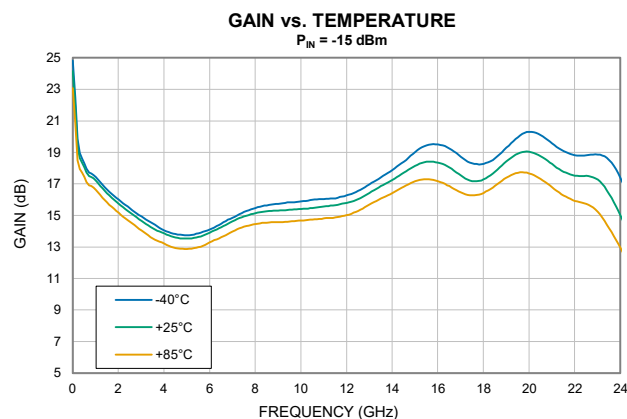
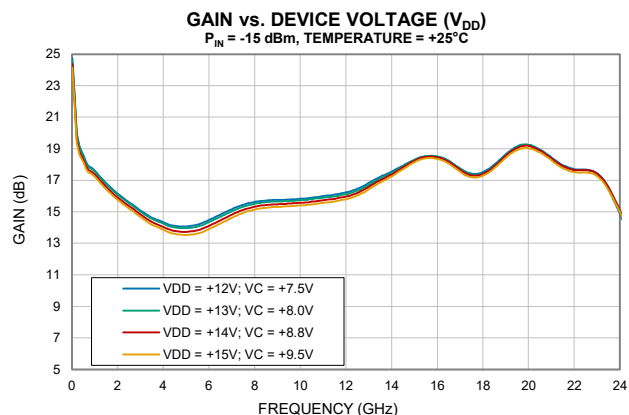
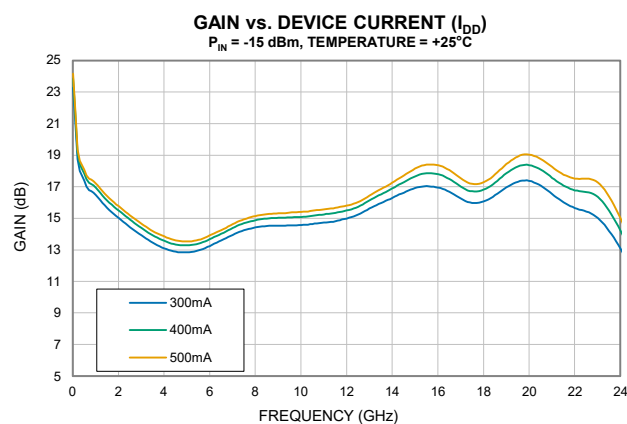
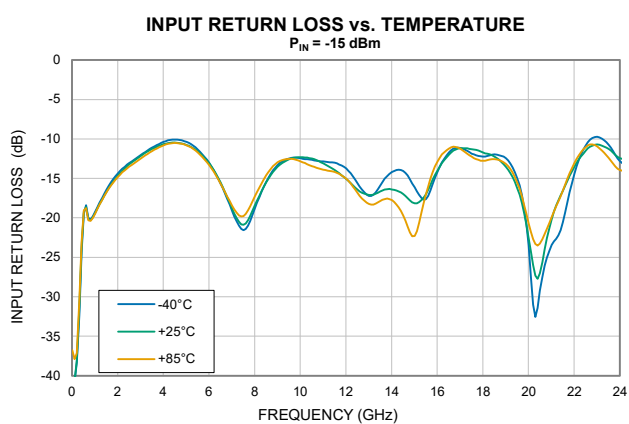
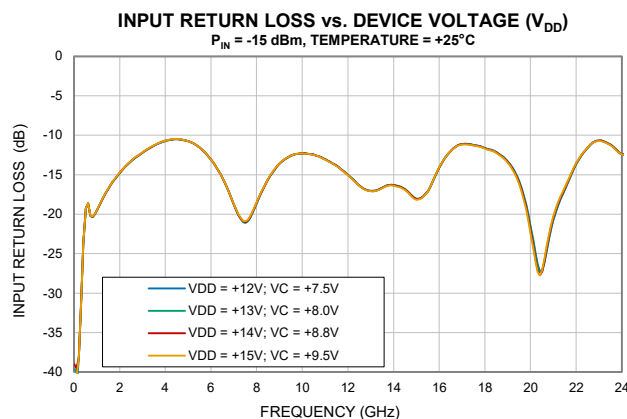
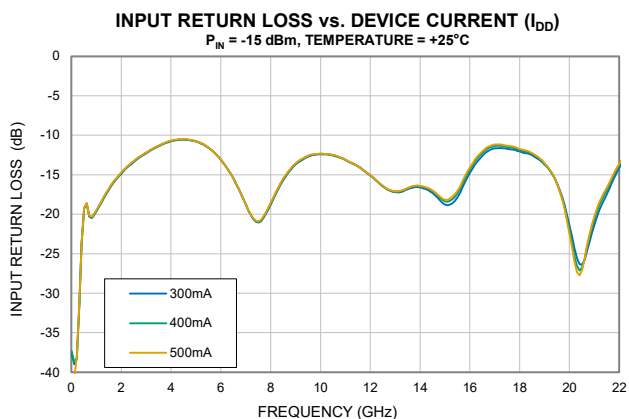


Typical Performance Curves

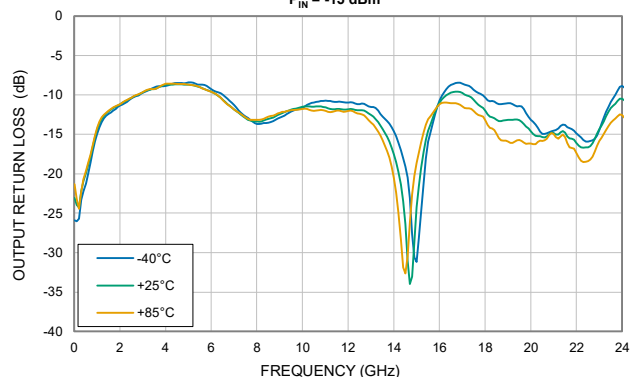
Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.



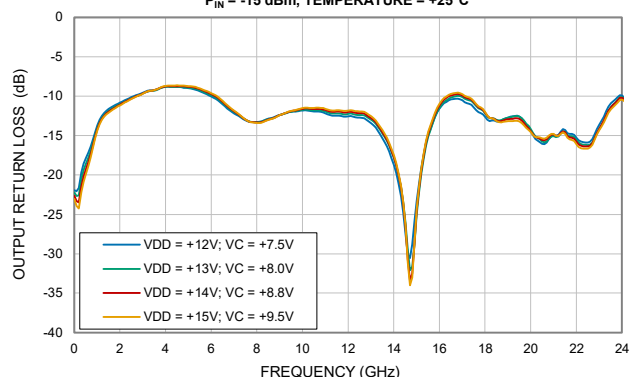
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.

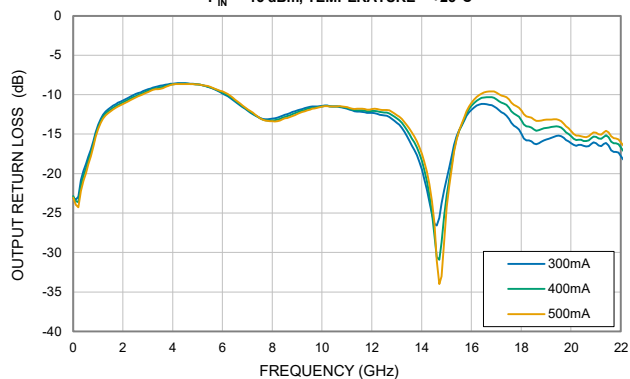
OUTPUT RETURN LOSS vs. TEMPERATURE
 $P_{IN} = -15\text{ dBm}$



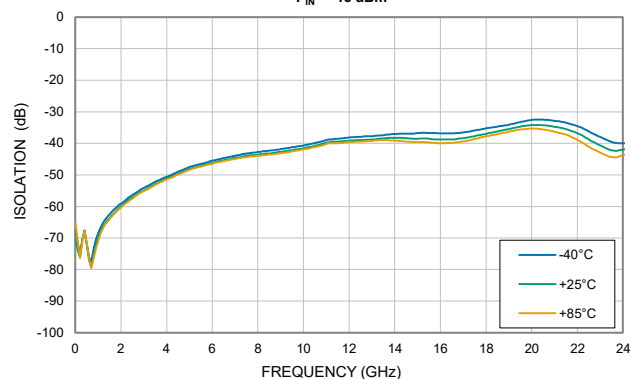
OUTPUT RETURN LOSS vs. DEVICE VOLTAGE (V_{DD})
 $P_{IN} = -15\text{ dBm}$, TEMPERATURE = +25°C



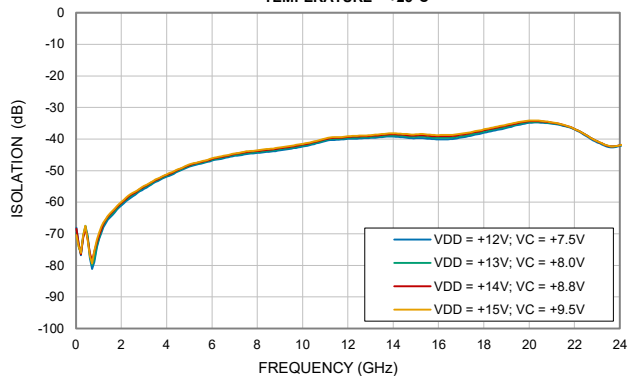
OUTPUT RETURN LOSS vs. DEVICE CURRENT (I_{DD})
 $P_{IN} = -15\text{ dBm}$, TEMPERATURE = +25°C



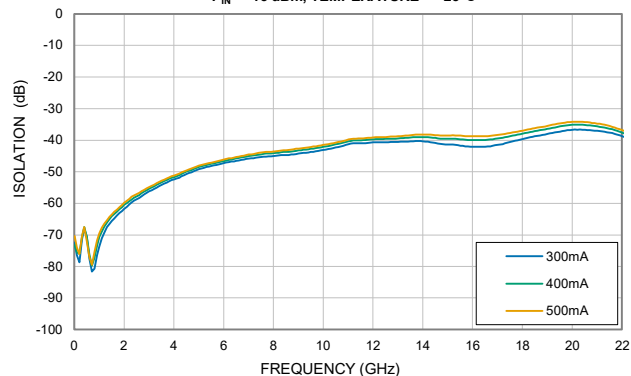
ISOLATION vs. TEMPERATURE
 $P_{IN} = -15\text{ dBm}$



ISOLATION vs. DEVICE VOLTAGE (V_{DD})
TEMPERATURE = +25°C

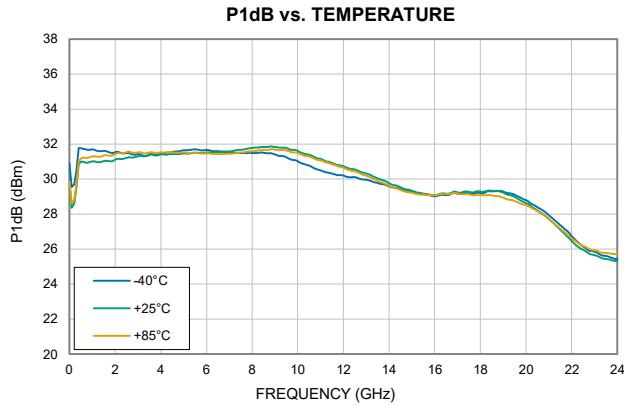
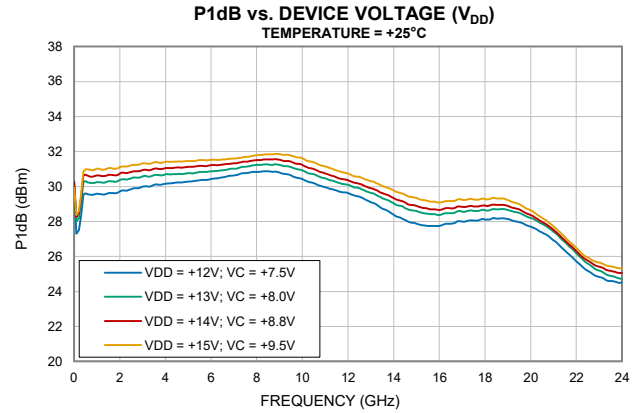
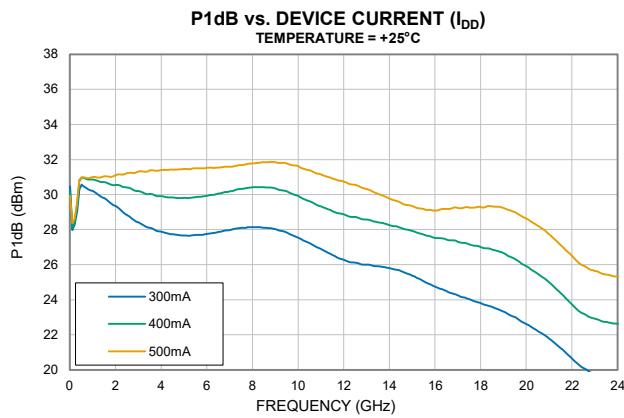
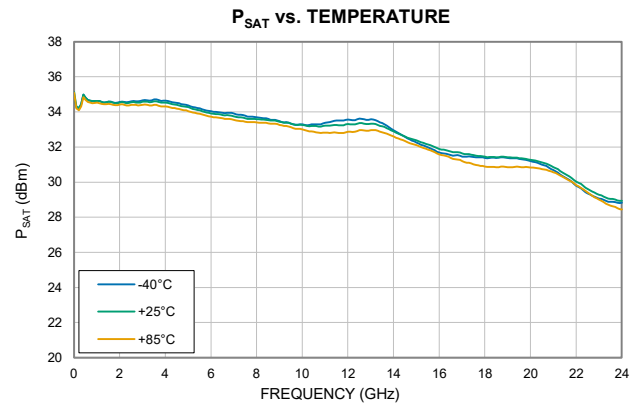
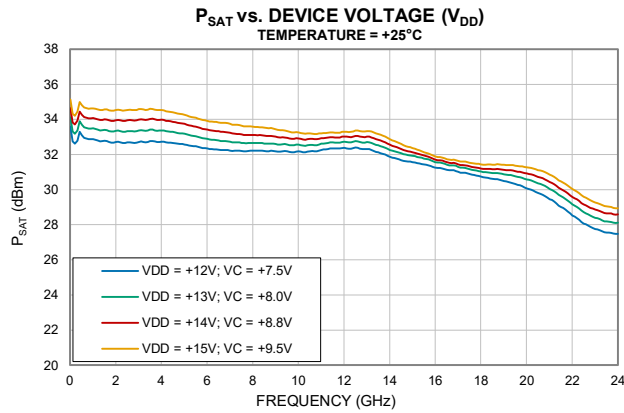
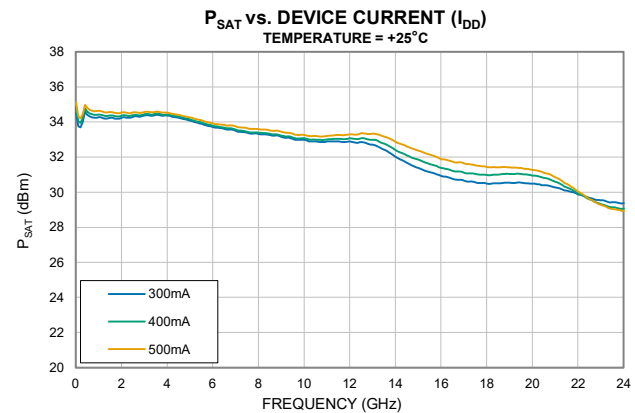


ISOLATION vs. DEVICE CURRENT (I_{DD})
 $P_{IN} = -15\text{ dBm}$, TEMPERATURE = +25°C



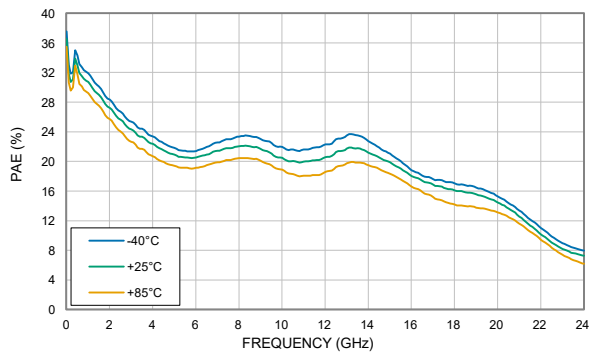
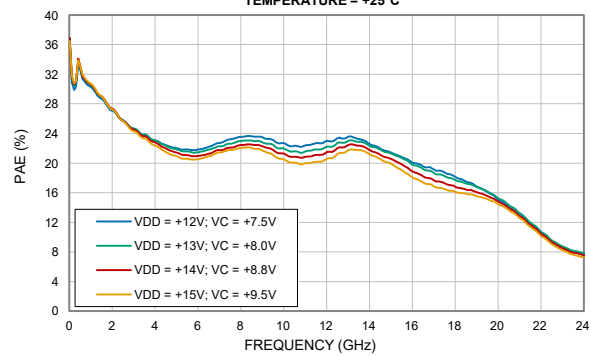
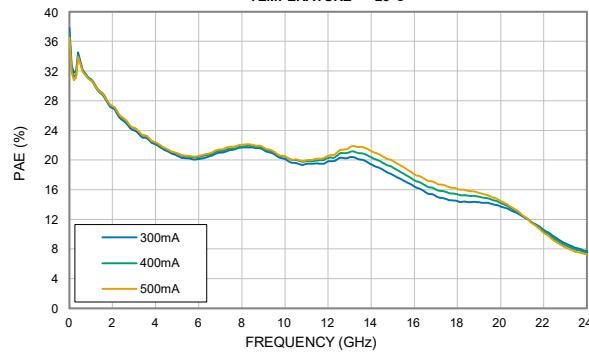
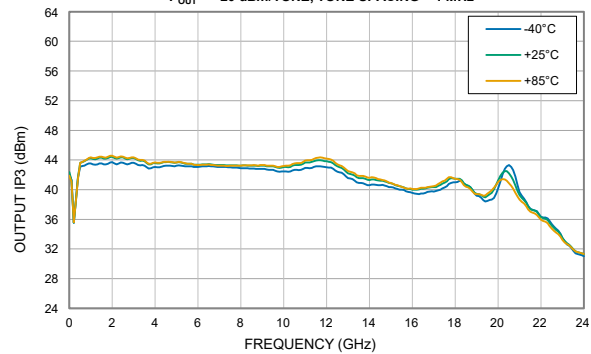
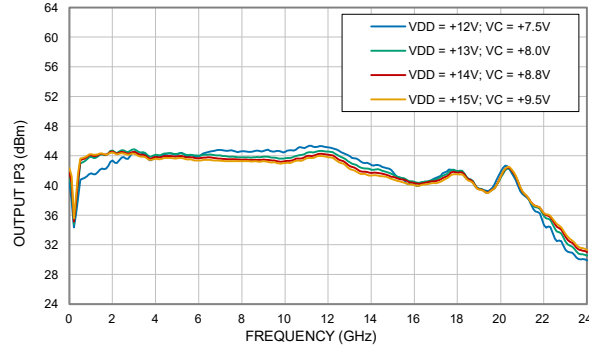
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.



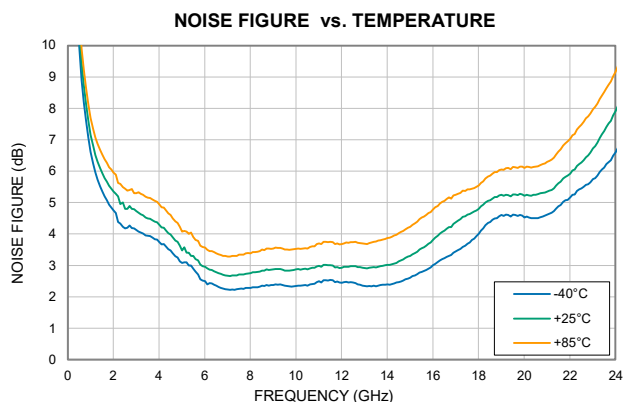
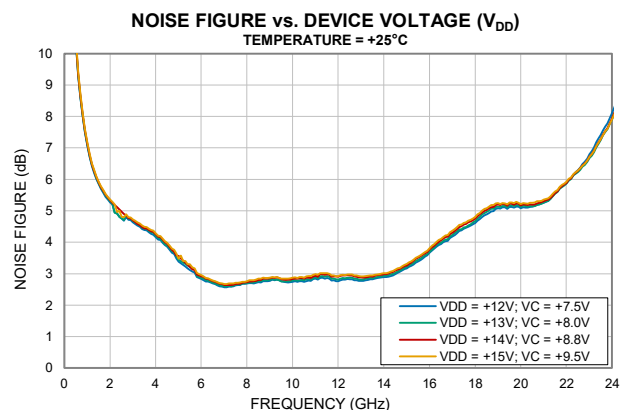
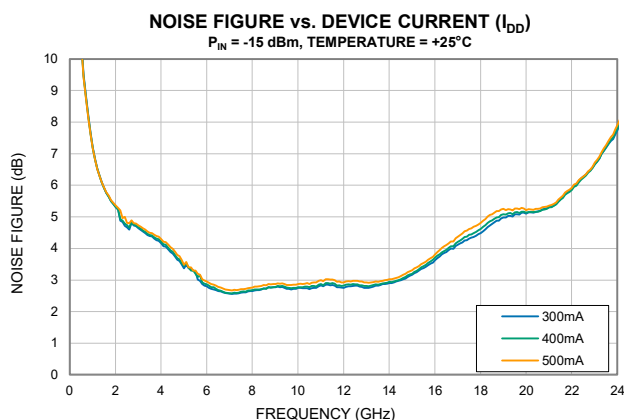
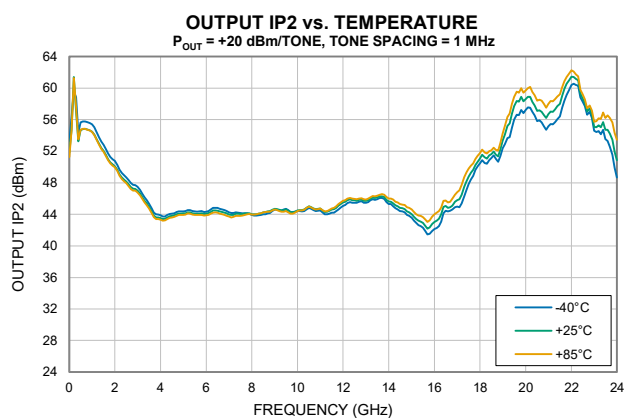
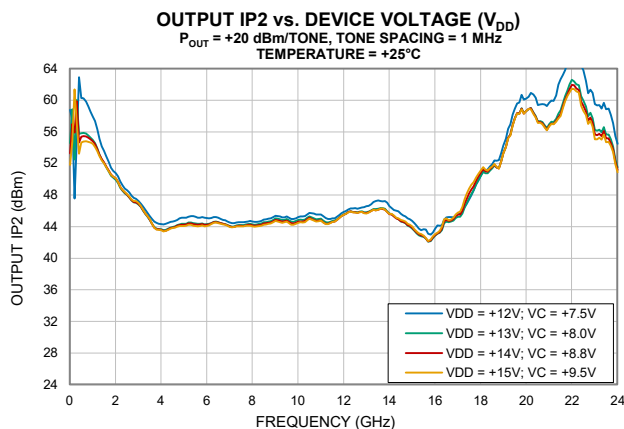
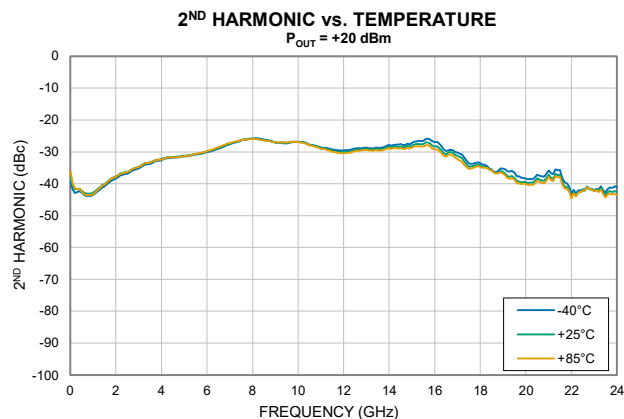
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.

PAE @ P_{SAT} vs. TEMPERATUREPAE @ P_{SAT} vs. DEVICE VOLTAGE (V_{DD})
TEMPERATURE = +25°CPAE @ P_{SAT} vs. DEVICE CURRENT (I_{DD})
TEMPERATURE = +25°COUTPUT IP3 vs. TEMPERATURE
 $P_{OUT} = +20\text{ dBm/TONE}$, TONE SPACING = 1 MHzOUTPUT IP3 vs. DEVICE VOLTAGE (V_{DD})
 $P_{OUT} = +20\text{ dBm/TONE}$, TONE SPACING = 1 MHz
TEMPERATURE = +25°C

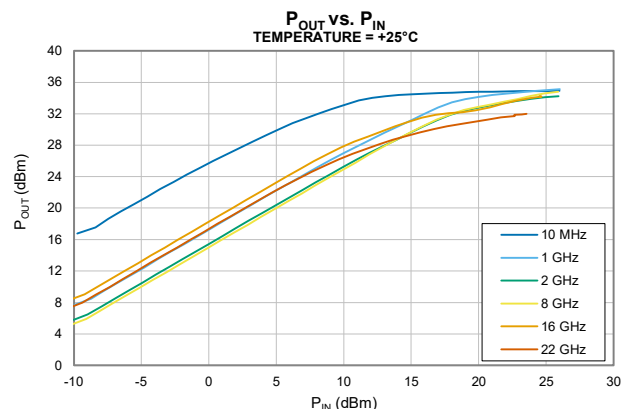
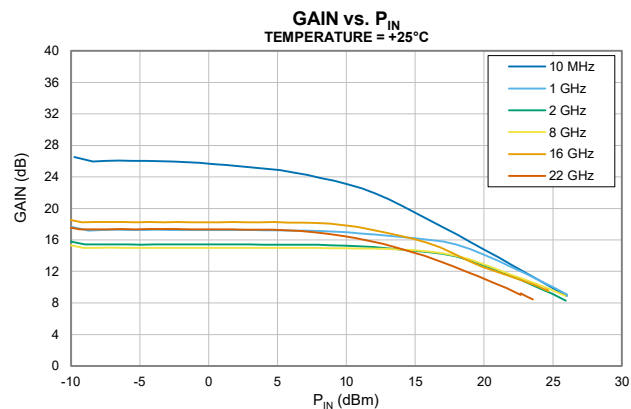
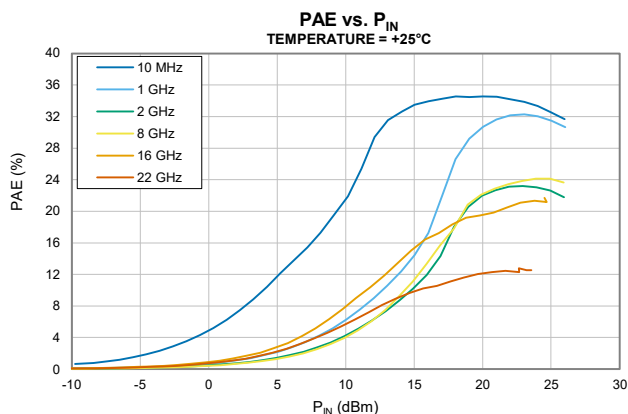
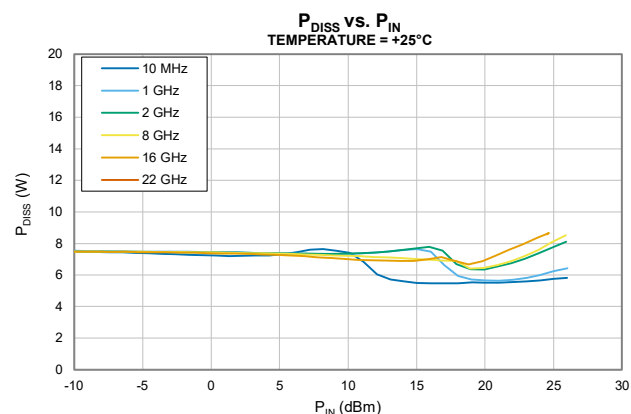
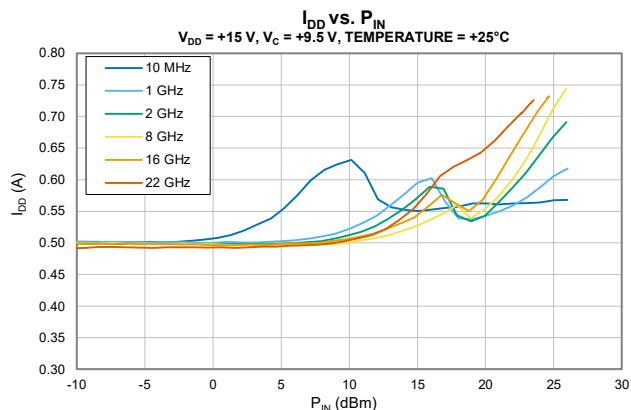
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.



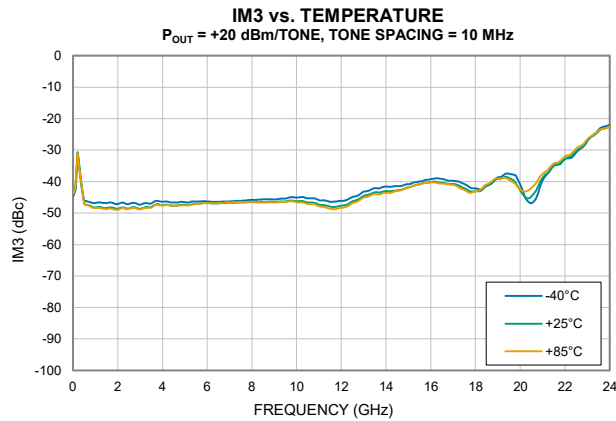
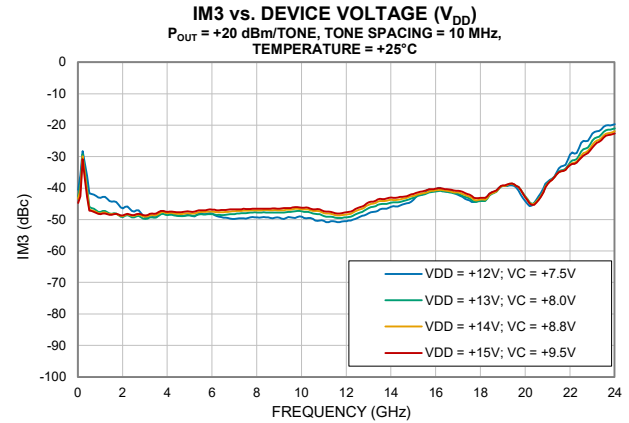
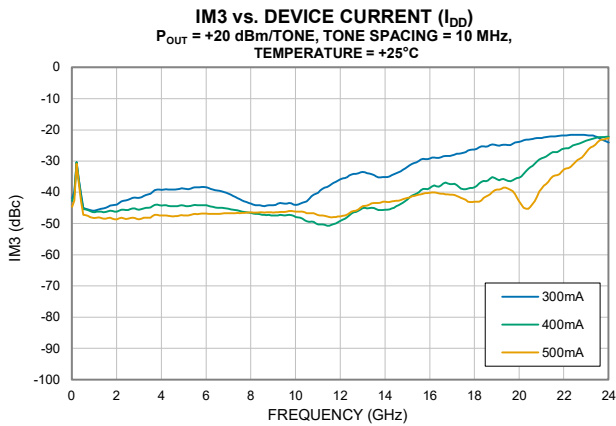
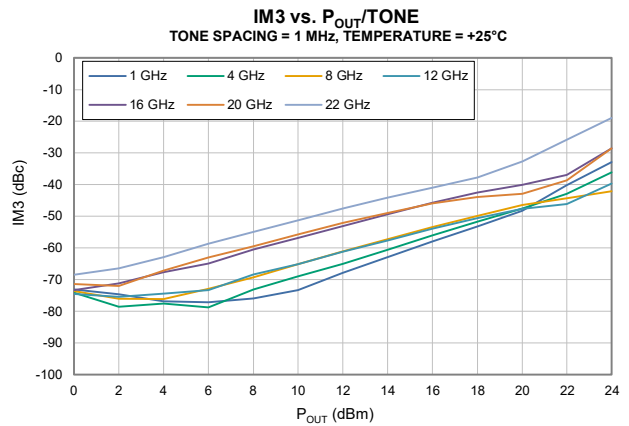
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.



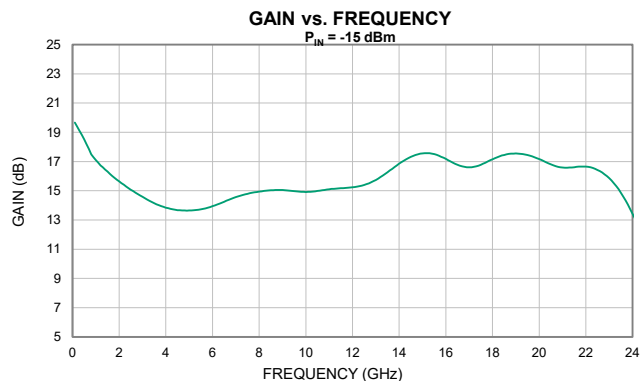
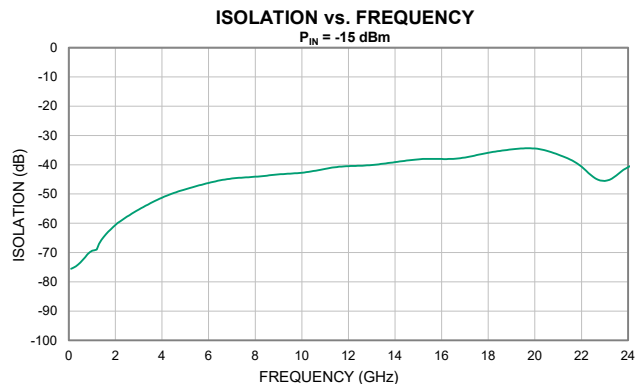
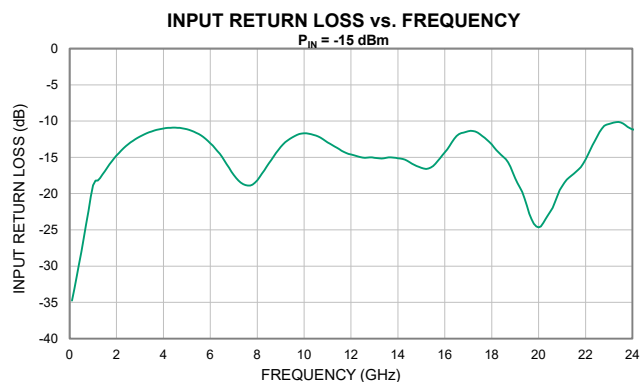
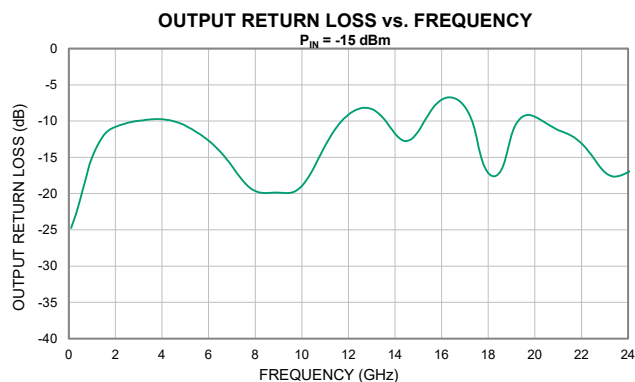
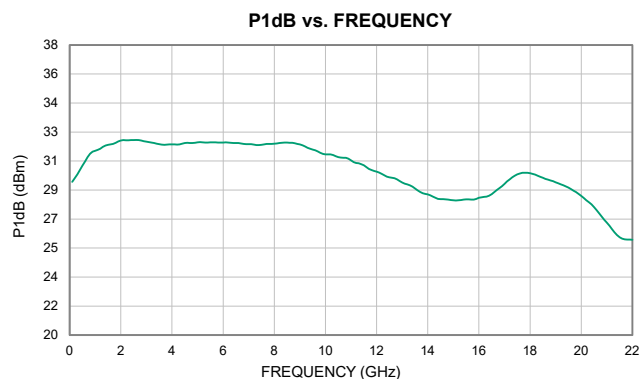
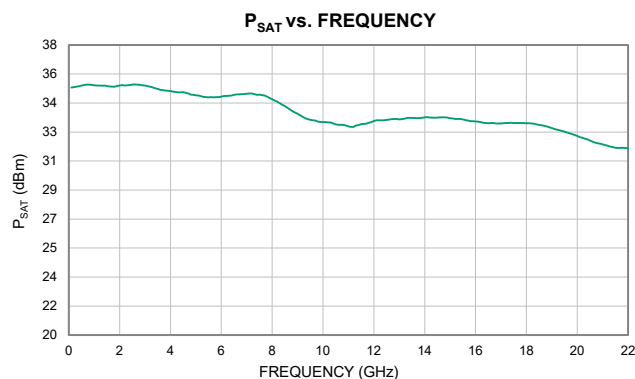
Typical Performance Curves

Note: The following data was taken on a Mini-Circuits Characterization Test Board with external Bias-T (Figure 2). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$ and $I_{DD} = 500\text{ mA}$ unless noted otherwise. V_G was adjusted at each voltage and temperature level to achieve $I_{DD} = 500\text{ mA}$.



Typical Performance Curves

Note: The following data was taken on Mini-Circuits Characterization Test Board TB-PMA5-223CX+ (Figure 3). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$, and Temperature = $+25^\circ\text{C}$ unless noted otherwise. V_G was adjusted to achieve $I_{DD} = 500\text{ mA}$.



Typical Performance Curves

Note: The following data was taken on Mini-Circuits Characterization Test Board TB-PMA5-223CX+ (Figure 3). All data taken at nominal condition of $V_{DD} = +15\text{ V}$, $V_C = +9.5\text{ V}$, and Temperature = $+25^\circ\text{C}$ unless noted otherwise. V_G was adjusted to achieve $I_{DD} = 500\text{ mA}$.

